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Attorney's Docket No. 5308-395

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Michael John O'Loughlin et al.

Confirmation No.: 1454

Serial No.: 10/790,406

Group Art Unit: 1765

Filed: March 1, 2004

Examiner: Nadine Georgianna Norton

For: *Reduction of Carrot Defects in Silicon Carbide Epitaxy*

Date: July 7, 2005

Mail Stop Amendment

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT  
FOR INTERNATIONAL SEARCH REPORT**

Sir:

Attached is a Supplemental Form PTO-1449 listing documents cited in the International Search Report for the corresponding International Application Number PCT/US2004/038895. Each document listed on the attached PTO-1449 was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Statement. A copy of any listed foreign patent document and/or non-patent literature, including the Search Report, is enclosed. A copy of any listed U.S. patent and/or U.S. patent application publication is not provided herewith in accordance with the amendment by the U.S. Patent and Trademark Office of requirements under 37 C.F.R. § 1.98(a)(2)(ii) effective October 21, 2004.

It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. §1.56 and Section 609 of the MPEP.

No fee is believed due; however, the Commissioner is hereby authorized to charge any deficiency or credit any refund to Deposit Account No. 50-0220.

Respectfully submitted,

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Sheena L. Donnelly

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Application Number	10/790,406
Filing Date	March 1, 2004
First Named Inventor	Michael John O'Loughlin
Group Art Unit	1765
Examiner Name	Nadine Georgianna Norton
Attorney Docket Number	5308-395

U.S. PATENTS AND PATENT PUBLICATIONS					
Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
	1.	US-2005/0064723		Sumakeris	03-24-2005
	2.	US-2003/0079689		Sumakeris et al.	05-01-2003
		US-			
		US-			
		US-			
		US-			

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OTHER NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
	5.	Ellison et al. "Epitaxial Growth of SiC in a Chimney CVD Reactor" <i>Journal of Crystal Growth</i> 236: 225-238 (2002)	
	6.	International Search Report and the Written Opinion of the International Searching Authority for International patent application no. PCT/US2004/038895 mailed on June 1, 2005	
	7.	Kimoto et al. "Homoeptaxial Growth of 4H-SiC(0 3 3 8) and Nitrogen Doping by Chemical Vapor Deposition" <i>Journal of Crystal Growth</i> 249: 208-215 (2003)	
	8.	Konstantinov et al. "The Mechanism for Cubic SiC Formation on Off-Oriented Substrates" <i>Journal of Crystal Growth</i> 178: 495-504 (1997)	
	9.	Mills "Wide Bandgaps Show Power Pedigree in San Francisco" <i>Meeting Report</i> 11(5): 46-51 (1998)	
	10.	Nakazawa et al. "High-purity 4H-Sic Epitaxial Growth by Hot-Wall Chemical Vapor Deposition" <i>Journal of Crystal Growth</i> 237-239: 1213-1218 (2002)	
	11.	Okada et al. "Correspondence Between Surface Morphological Faults And Crystallographic Defects In 4H-SiC Homoepitaxial Film" <i>Jpn J Appl Physics</i> 41: 6320-6326 (2002)	
	12.	Wahab et al. "Influence of Epitaxial Growth and Substrate-Induced Defects on the Breakdown of 4H-SiC Schottky Diodes" <i>Applied Physics Letters</i> 76(19): 2725-2727 (2000)	

Date Considered

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.